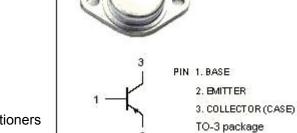


# **Silicon PNP Power Transistor**

**MJ21193** 

#### **DESCRIPTION**

- · Excellent Safe Operating Area
- DC Current Gain-
  - :  $h_{FE}$ = 25-75@ $I_C$  = -8A, $V_{CE}$ =-5V
- · Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)}$ = -1.4 V(Max)@  $I_C$  = -8A
- Complement to the NPN MJ21194
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

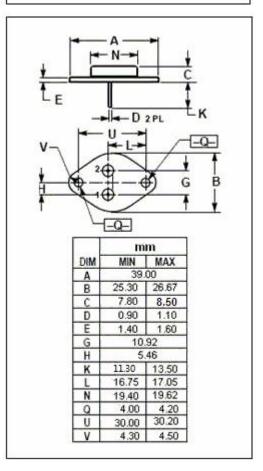
• Designed for high power audio output, disk head positioners and other linear applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-250	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current-Continuous	-16	Α
I <sub>B</sub>	Base Current -5		Α
P <sub>D</sub>	Total Power Dissipation@Tc=25°C	250	W
Tj	Junction Temperature	200	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature	-65~200	$^{\circ}$ C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.7	°C/W





# Silicon PNP Power Transistor

**MJ21193** 

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -50mA ;I <sub>B</sub> = 0	-250		٧
VCE(sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.8A		-1.4	٧
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	Ic= -16A; I <sub>B</sub> = -3.2A		-4.0	٧
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> =8A ; V <sub>CE</sub> = 5V		-2.2	٧
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -200V; V <sub>BE(off)</sub> = 0		-0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-0.1	mA
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -8A ; V <sub>CE</sub> = -5V	25	75	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -16A; V <sub>CE</sub> = -5V	8		
I <sub>s/b</sub>	Second Breakdown Collector Current with Base Forward Biased	V <sub>CE</sub> = -50Vdc,t= 1 s,Nonrepetitive	-5		Α
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = -10V; f <sub>test</sub> = -1.0MHz	300		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -10V; f <sub>test</sub> = -1.0MHz	4		MHz

### NOTICE:

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